Silicon Schottky Barrier Diode for System Protection

# **HITACHI**

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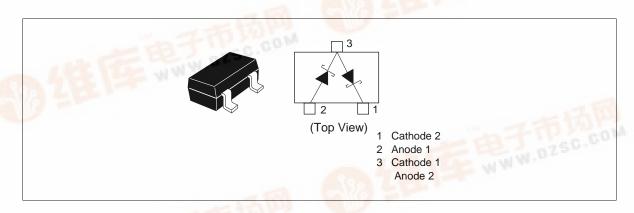
#### **Features**

- Low V<sub>F</sub> and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.

#### **Ordering Information**

Type No.	Laser Mark	Package Code
HSM107S	C5	MPAK

#### **Outline**





## Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Item	Symbol	Value	Unit	
Reverse voltage	$V_R$	8	V	
Peak forward current	I <sub>FM</sub>	0.1	Α	_
Non-Repetitive Peak forward surge current	I <sub>FSM</sub> *1	0.5	А	
Average forward current	Io	50	mA	_
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	-55 to +125	°C	

Notes: 1. Square wave, 10ms

### **Electrical Characteristics (Ta = 25^{\circ}C)**

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse voltage	$V_R$	8	_	_	_	I <sub>R</sub> = 1.0 mA
Reverse current	I <sub>R</sub>	_	_	30	μΑ	V <sub>R</sub> = 5 V
Forward voltage	V <sub>F</sub>	_	_	0.3	V	I <sub>F</sub> = 10 mA
ESD Capability *1	_	100	_	_	V	C=200pF, Both forward and reverse direction 1 pulse

Notes: 1. Failure Criterion ;  $I_R \ge 60\mu A$  at  $V_R = 5V$ 

#### **Main Characteristic**

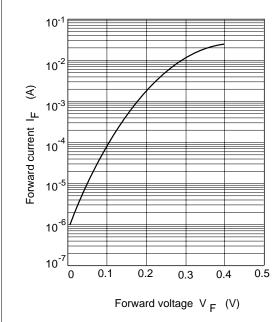
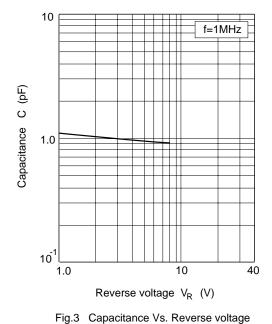


Fig.1 Forward current Vs. Forward voltage

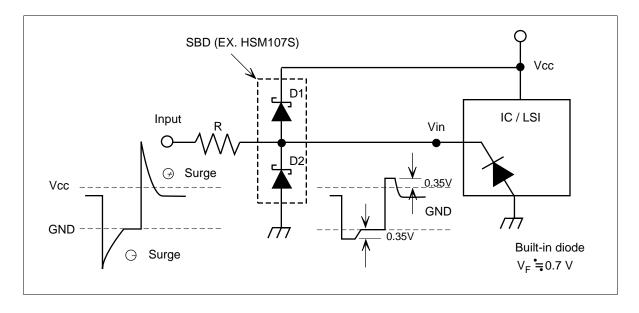


10<sup>-2</sup>
(V) 10<sup>-3</sup>
10<sup>-4</sup>
10<sup>-6</sup>
0 2 4 6 8 10

Reverse voltage V<sub>R</sub> (V)

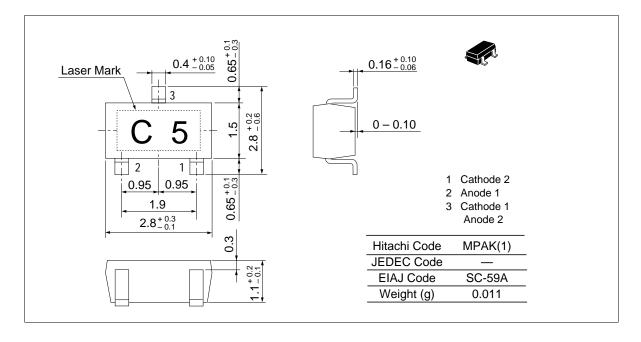
Fig.2 Reverse current Vs. Reverse voltage

## Example of application circuite



## **Package Dimensions**

Unit: mm



#### **Cautions**

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